Designed to Reduce Reflection Noise

- Repetitive Peak Forward Current to 200 mA
- 12-Bit Array Structure Suited for Bus-Oriented Systems

description/ordering information

This Schottky barrier diode bus-termination array is designed to reduce reflection noise on memory bus lines. This device consists of a 12-bit high-speed Schottky diode array suitable for clamping to V_{CC} and/or GND.

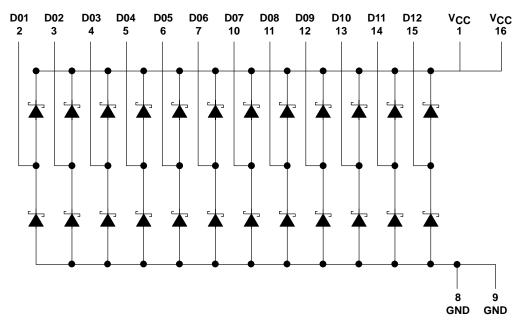
D, N, NS, OR PW PACKAGE (TOP VIEW)								
V _{CC} [1 D01[2 D02[3 D03[4 D04[5 D05[6 D06[7 GND[8	14 13 12	V _{CC} D12 D11 D10 D09 D08 D07 GND						

Τ _Α	PACK	AGE [†]	ORDERABLE PART NUMBER	TOP-SIDE MARKING				
0°C to 70°C	PDIP – N	Tube	SN74S1051N	SN74S1051N				
	SOIC - D	Tube	SN74S1051D	S1051				
	50IC - D	Tape and reel	SN74S1051DR	51051				
	SOP – NS	Tape and reel	SN74S1051NSR	74S1051				
L	TSSOP – PW	Tape and reel	SN74S1051PWR	S1051				

ORDERING INFORMATION

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

schematic diagrams





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



Copyright © 2003, Texas Instruments Incorporated

1

SN74S1051 **12-BIT SCHOTTKY BARRIER DIODE BUS-TERMINATION ARRAY**

SDLS018B – SEPTEMBER 1990 – REVISED MARCH 2003

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Steady-state reverse voltage, V _R	7 V
Continuous forward current, I _F : Any D terminal from GND or to V _{CC}	
Total through all GND or V _{CC} terminals	
Repetitive peak forward current [‡] , I _{FRM} : Any D terminal from GND or V _{CC}	
Total through all GND or V _{CC} terminals	1 A
Package thermal impedance, θ_{JA} (see Note 1): D package	73°C/W
N package	
NS package	
PW package	
Operating free-air temperature range	
Storage temperature range, T _{stg}	
† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress r	atings only, and
functional operation of the device at these or any other conditions beyond those indicated under "recommended operating co	onditions" is not
implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.	
[‡] These values apply for t _w < 100 µs, duty cycle < 20%.	

[‡]These values apply for $t_W \le 100 \ \mu$ s, duty cycle $\le 20\%$.

NOTE 1: The package thermal impedance is calculated in accordance with JESD 51-7.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

single-diode operation (see Note 2)

PARAMETER		TEST C	MIN TYP§	MAX	UNIT		
			I _F = 18 mA	0.85	1.05		
\/-	Static forward voltage	To VCC	I _F = 50 mA	1.05	1.3	v	
VF Static forward voltage	From CND	I _F = 18 mA	0.75	0.95			
		From GND	I _F = 50 mA	0.95	1.2		
$V_{\sf FM}$	Peak forward voltage		I _F = 200 mA	1.45		V	
-	Static reverse current	To V _{CC}	V _R = 7 V		5	μA	
IR Static reve	Static reverse current	From GND	vR = 7 v		5	μΑ	
C _t	Total capacitance	V _R = 0 V,	f = 1 MHz	8	16	pF	
		V _R = 2 V,	f = 1 MHz	4	8	p	

§ All typical values are at $V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}C$.

NOTE 2: Test conditions and limits apply separately to each of the diodes. The diodes not under test are open-circuited during the measurement of these characteristics.

multiple-diode operation

		PARAMETER	TEST CON	MIN	TYP§	MAX	UNIT
	I _X Internal crosstalk current	Total I _F current = 1 A,	See Note 3		0.8	2	m A
		Internal crossialk culterit	Total I _F current = 198 mA,	See Note 3		0.02	0.2

 $\overline{$ All typical values are at V_{CC} = 5 V, T_A = 25°C.

NOTE 3: I_X is measured under the following conditions with one diode static, all others switching:

Switching diodes: $t_W = 100 \ \mu s$, duty cycle = 20%

Static diode: $V_R = 5 V$

The static diode input current is the internal crosstalk current, I_x.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 and 2)

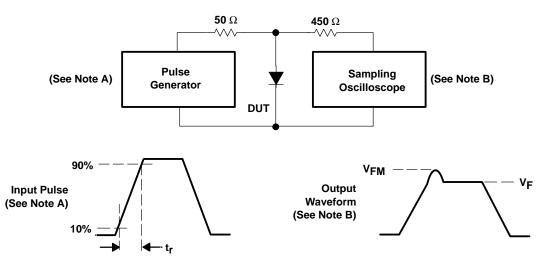
	PARAMETER		MIN	TYP	MAX	UNIT			
t _{rr}	Reverse recovery time	I _F = 10 mA,	I _{RM(REC)} = 10 mA,	$I_{R(REC)} = 1 \text{ mA},$	$R_L = 100 \Omega$		8	16	ns



SN74S1051 **12-BIT SCHOTTKY BARRIER DIODE** -TERMINATION ARRAY BUS

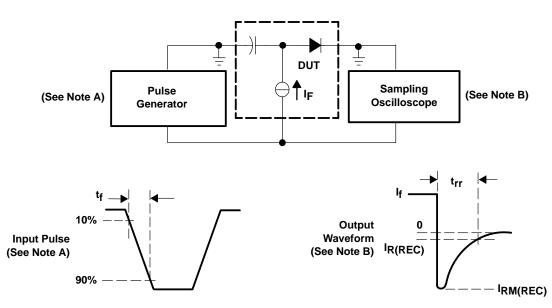
SDLS018B - SEPTEMBER 1990 - REVISED MARCH 2003

PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The input pulse is supplied by a pulse generator having the following characteristics: $t_r = 20$ ns, $Z_O = 50 \Omega$, freq = 500 Hz, duty cycle = 1%.
 - B. The output waveform is monitored by an oscilloscope having the following characteristics: $t_f \le 350$ ps, $R_j = 50 \Omega$, $C_j \le 5$ pF.

Figure 1. Forward Recovery Voltage



- NOTES: A. The input pulse is supplied by a pulse generator having the following characteristics: $t_f = 0.5$ ns, $Z_O = 50 \Omega$, $t_W \ge 50$ ns, duty cycle = 1%.
 - B. The output waveform is monitored by an oscilloscope having the following characteristics: $t_r \le 350$ ps, $R_i = 50 \Omega$, $C_i \le 5$ pF.

Figure 2. Reverse Recovery Time



SN74S1051 12-BIT SCHOTTKY BARRIER DIODE BUS-TERMINATION ARRAY

SDLS018B - SEPTEMBER 1990 - REVISED MARCH 2003

APPLICATION INFORMATION

Large negative transients at the inputs of memory devices (DRAMs, SRAMs, EPROMs, etc.) or on the CLOCK lines of many clocked devices can result in improper operation of the devices. The SN74S1051 diode termination array helps suppress negative transients caused by transmission-line reflections, crosstalk, and switching noise.

Diode terminations have several advantages when compared to resistor termination schemes. Split-resistor or Thevenin-equivalent termination can cause a substantial increase in power consumption. The use of a single resistor to ground to terminate a line usually results in degradation of the output high level, resulting in reduced noise immunity. Series damping resistors placed on the outputs of the driver reduce negative transients, but they also can increase propagation delays down the line because a series resistor reduces the output drive capability of the driving device. Diode terminations have none of these drawbacks.

The operation of the diode arrays in reducing negative transients is explained in the following figures. The diode conducts current when the voltage reaches a negative value large enough for the diode to turn on. Suppression of negative transients is tracked by the current-voltage characteristic curve for that diode. Typical current-versus-voltage curves for the SN74S1051 are shown in Figures 3 and 4.

To illustrate how the diode arrays act to reduce negative transients at the end of a transmission line, the test setup in Figure 5 was evaluated. The resulting waveforms with and without the diode are shown in Figure 6.

The maximum effectiveness of the diode arrays in suppressing negative transients occurs when the diode arrays are placed at the end of a line and/or the end of a long stub branching off a main transmission line. The diodes can also reduce the negative transients that occur due to discontinuities in the middle of a line. An example of this is a slot in a backplane that is provided for an add-on card.

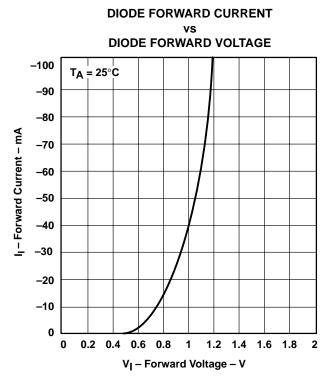


Figure 3. Typical Input Current vs Input Voltage (Lower Diode)



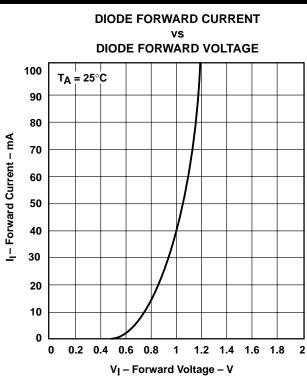
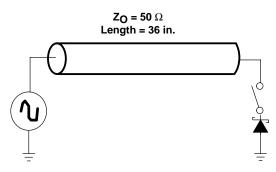


Figure 4. Typical Input Current vs Input Voltage (Upper Diode)



APPLICATION INFORMATION





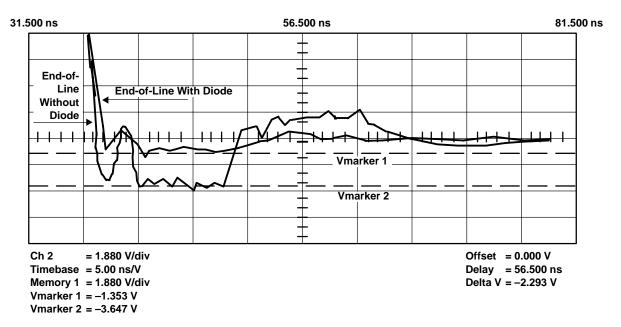


Figure 6. Reduction of Negative Transients at the End of a Transmission Line



PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
SN74S1051D	ACTIVE	SOIC	D	16	40	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1 YEAR/ Level-1-235C-UNLIM
SN74S1051DR	ACTIVE	SOIC	D	16	2500	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1 YEAR/ Level-1-235C-UNLIM
SN74S1051N	ACTIVE	PDIP	Ν	16	25	Pb-Free (RoHS)	CU NIPDAU	Level-NC-NC-NC
SN74S1051NSR	ACTIVE	SO	NS	16	2000	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1 YEAR/ Level-1-235C-UNLIM
SN74S1051PW	ACTIVE	TSSOP	PW	16	90	Pb-Free (RoHS)	CU NIPDAU	Level-1-250C-UNLIM
SN74S1051PWR	ACTIVE	TSSOP	PW	16	2000	Pb-Free (RoHS)	CU NIPDAU	Level-1-250C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - May not be currently available - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

None: Not yet available Lead (Pb-Free).

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Green (RoHS & no Sb/Br): TI defines "Green" to mean "Pb-Free" and in addition, uses package materials that do not contain halogens, including bromine (Br) or antimony (Sb) above 0.1% of total product weight.

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDECindustry standard classifications, and peak solder temperature.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



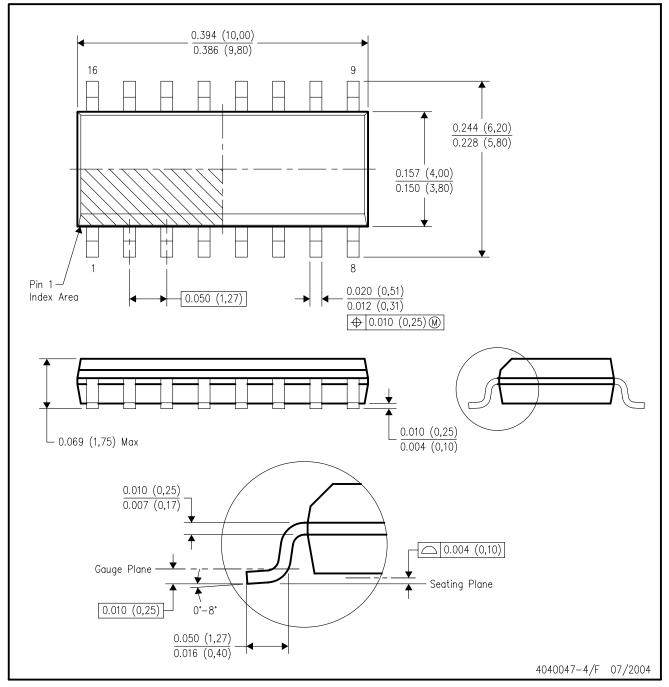
NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- \triangle The 20 pin end lead shoulder width is a vendor option, either half or full width.



D (R-PDSO-G16)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).

D. Falls within JEDEC MS-012 variation AC.



MECHANICAL DATA

PLASTIC SMALL-OUTLINE PACKAGE

0,51 0,35 ⊕0,25⊛ 1,27 8 14 0,15 NOM 5,60 8,20 5,00 7,40 \bigcirc Gage Plane ₽ 0,25 7 1 1,05 0,55 0°-10° Δ 0,15 0,05 Seating Plane — 2,00 MAX 0,10PINS ** 14 16 20 24 DIM 10,50 10,50 12,90 15,30 A MAX A MIN 9,90 9,90 12,30 14,70 4040062/C 03/03

NOTES: A. All linear dimensions are in millimeters.

NS (R-PDSO-G**)

14-PINS SHOWN

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



MECHANICAL DATA

MTSS001C - JANUARY 1995 - REVISED FEBRUARY 1999

PW (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

14 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
- D. Falls within JEDEC MO-153



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

Products		Applications	
Amplifiers	amplifier.ti.com	Audio	www.ti.com/audio
Data Converters	dataconverter.ti.com	Automotive	www.ti.com/automotive
DSP	dsp.ti.com	Broadband	www.ti.com/broadband
Interface	interface.ti.com	Digital Control	www.ti.com/digitalcontrol
Logic	logic.ti.com	Military	www.ti.com/military
Power Mgmt	power.ti.com	Optical Networking	www.ti.com/opticalnetwork
Microcontrollers	microcontroller.ti.com	Security	www.ti.com/security
		Telephony	www.ti.com/telephony
		Video & Imaging	www.ti.com/video
		Wireless	www.ti.com/wireless

Mailing Address:

Texas Instruments

Post Office Box 655303 Dallas, Texas 75265

Copyright © 2005, Texas Instruments Incorporated